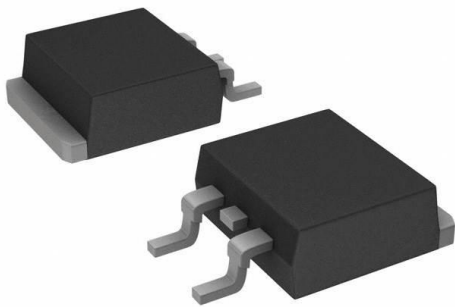


SPB100N06S2L-05 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	SPB100N06S2L-05-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	SPB100N06S2L-05
Description	MOSFET N-CH 55V 100A TO263-3
Detailed Description	N-Channel 55 V 100A (Tc) 300W (Tc) Surface Mount PG-TO263-3-2



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

SPB100N06S2L-05

Series:

OptiMOS™

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

55 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2V @ 250µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

PG-T0263-3-2

Base Product Number:

SPB100N

Manufacturer:

Infineon Technologies

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

100A (Tc)

Rds On (Max) @ Id, Vgs:

4.4mOhm @ 80A, 10V

Gate Charge (Qg) (Max) @ Vgs:

230 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

7530 pF @ 25 V

Power Dissipation (Max):

300W (Tc)

Mounting Type:

Surface Mount

Package / Case:

TO-263-3, D2PAK (2 Leads + Tab), TO-263AB

Environmental & Export classification

RoHS Status:

RoHS non-compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



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SPB100N06S2L-05

OptiMOS® Power-Transistor

Feature

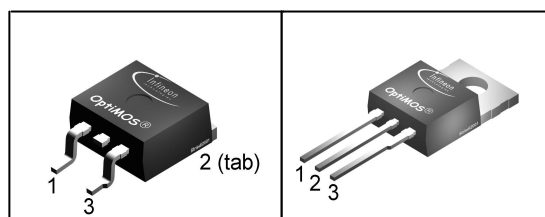
- N-Channel
- Enhancement mode
- Logic Level
- 175°C operating temperature
- Avalanche rated
- dv/dt rated

Product Summary

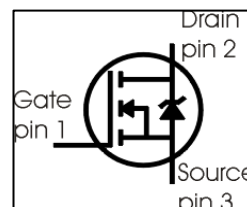
V_{DS}	55	V
$R_{DS(on)}$ max. SMD version	4.4	m Ω
I_D	100	A

P- TO263 -3-2

P- TO220 -3-1



Type	Package	Ordering Code	Marking
SPP100N06S2L-05	P- TO220 -3-1	Q67060-S6043	PN06L05
SPB100N06S2L-05	P- TO263 -3-2	Q67060-S6042	PN06L05



Maximum Ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current 1) $T_C=25^\circ\text{C}$	I_D	100 100	A
Pulsed drain current $T_C=25^\circ\text{C}$	$I_{D\text{ puls}}$	400	
Avalanche energy, single pulse $I_D=80\text{A}$, $V_{DD}=25\text{V}$, $R_{GS}=25\Omega$	E_{AS}	810	mJ
Repetitive avalanche energy, limited by $T_{j\text{max}}^{2)}$	E_{AR}	30	
Reverse diode dv/dt $I_S=100\text{A}$, $V_{DS}=44\text{V}$, $dI/dt=200\text{A}/\mu\text{s}$, $T_{j\text{max}}=175^\circ\text{C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_C=25^\circ\text{C}$	P_{tot}	300	W
Operating and storage temperature	T_j, T_{stg}	-55... +175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/175/56	



SPP100N06S2L-05
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Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	0.3	0.5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ³⁾	R_{thJA}	-	-	62 40	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=1mA$	$V_{(BR)DSS}$	55	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 250\mu A$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS}=55V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=55V, V_{GS}=0V, T_j=125^\circ C$	I_{DSS}	-	0.01 1	1 100	μA
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	1	100	
Drain-source on-state resistance $V_{GS}=4.5V, I_D=80A$ $V_{GS}=4.5V, I_D=80A, \text{SMD version}$	$R_{DS(on)}$	-	4.3 4	5.9 5.6	m Ω
Drain-source on-state resistance $V_{GS}=10V, I_D=80A$ $V_{GS}=10V, I_D=80A, \text{SMD version}$	$R_{DS(on)}$	-	3.5 3.2	4.7 4.4	

¹Current limited by bondwire ; with an $R_{thJC} = 0.5K/W$ the chip is able to carry $I_D = 175A$ at $25^\circ C$, for detailed information see app.-note ANPS071E available at www.infineon.com/optimos

²Defined by design. Not subject to production test.

³Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.


SPP100N06S2L-05
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Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 100A$	88	176	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = 25V$, $f = 1MHz$	-	5660	7530	pF
Output capacitance	C_{oss}		-	1330	1760	
Reverse transfer capacitance	C_{rss}		-	360	540	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V$, $V_{GS} = 4.5V$, $I_D = 100A$, $R_G = 1.3\Omega$	-	18	27	ns
Rise time	t_r		-	25	38	
Turn-off delay time	$t_{d(off)}$		-	98	150	
Fall time	t_f		-	24	36	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 44V$, $I_D = 100A$	-	19	25	nC
Gate to drain charge	Q_{gd}		-	57	90	
Gate charge total	Q_g	$V_{DD} = 44V$, $I_D = 100A$, $V_{GS} = 0$ to $10V$	-	170	230	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 44V$, $I_D = 100A$	-	3.3	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25^\circ C$	-	-	100	A
Inv. diode direct current, pulsed	I_{SM}		-	-	400	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0V$, $I_F = 80A$	-	0.9	1.3	V
Reverse recovery time	t_{rr}	$V_R = 30V$, $I_F = I_S$, $di_F/dt = 100A/\mu s$	-	65	80	ns
Reverse recovery charge	Q_{rr}		-	125	160	

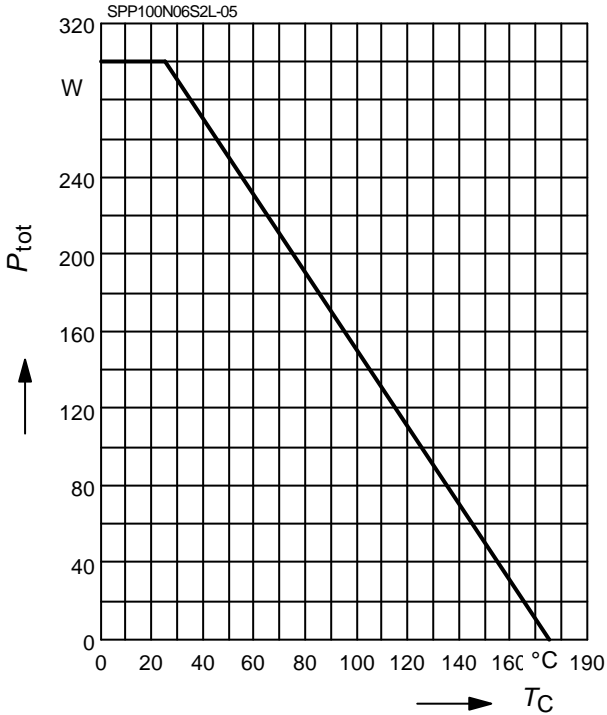


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1 Power dissipation

$P_{tot} = f(T_C)$

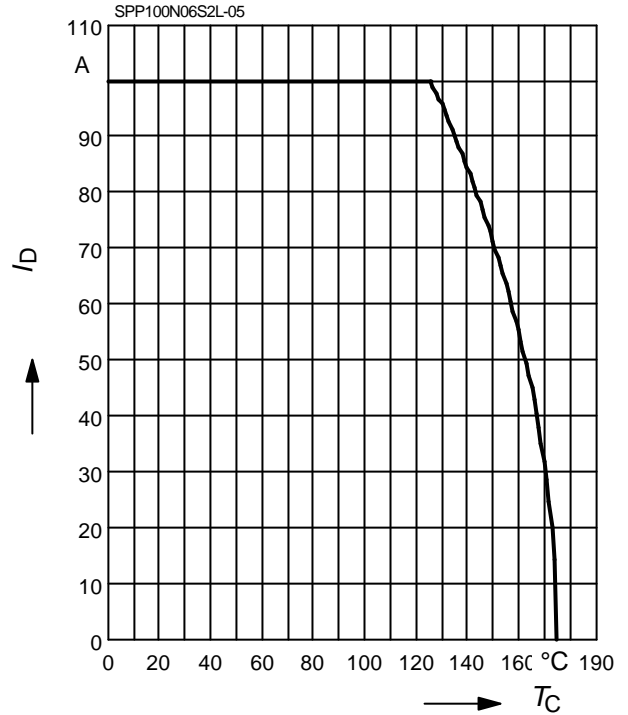
parameter: $V_{GS} \geq 4\text{ V}$



2 Drain current

$I_D = f(T_C)$

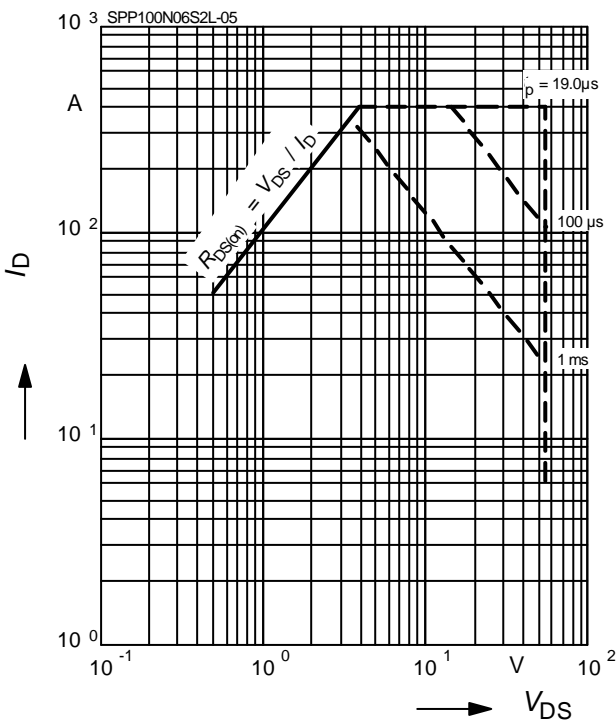
parameter: $V_{GS} \geq 10\text{ V}$



3 Safe operating area

$I_D = f(V_{DS})$

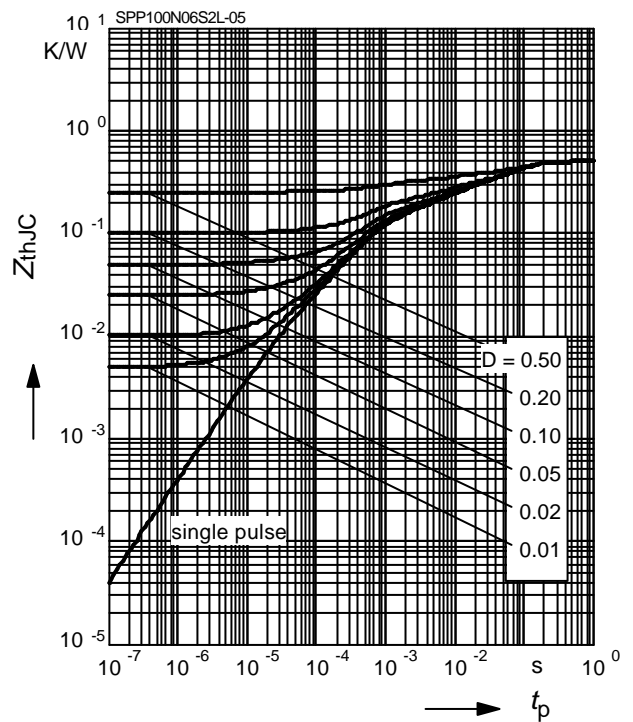
parameter: $D = 0, T_C = 25\text{ °C}$



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

parameter: $D = t_p/T$



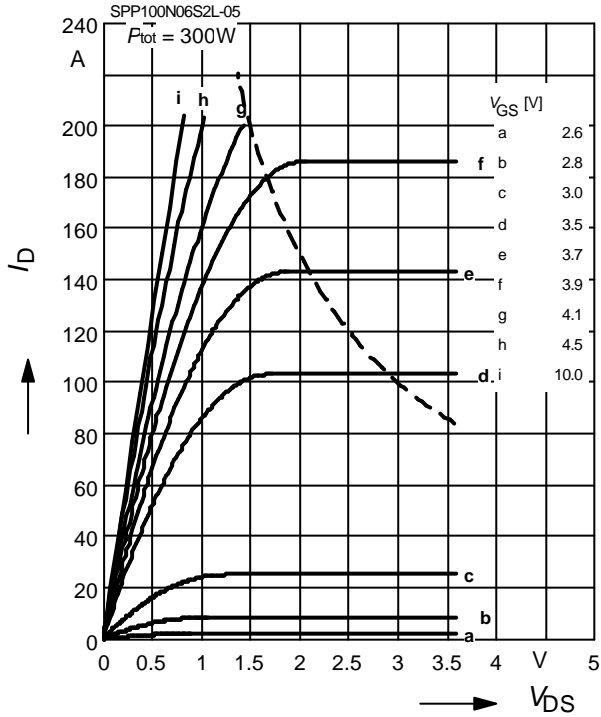


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5 Typ. output characteristic

$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$

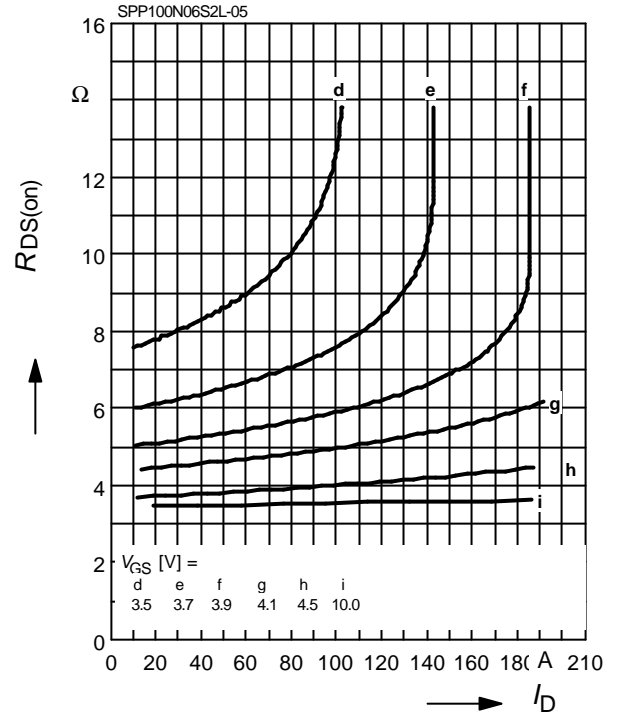
parameter: $t_p = 80 \mu\text{s}$



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

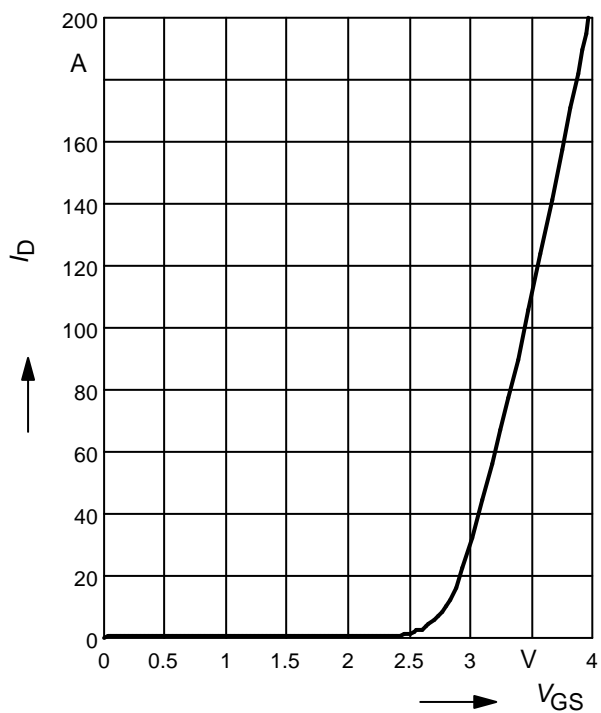
parameter: V_{GS}



7 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

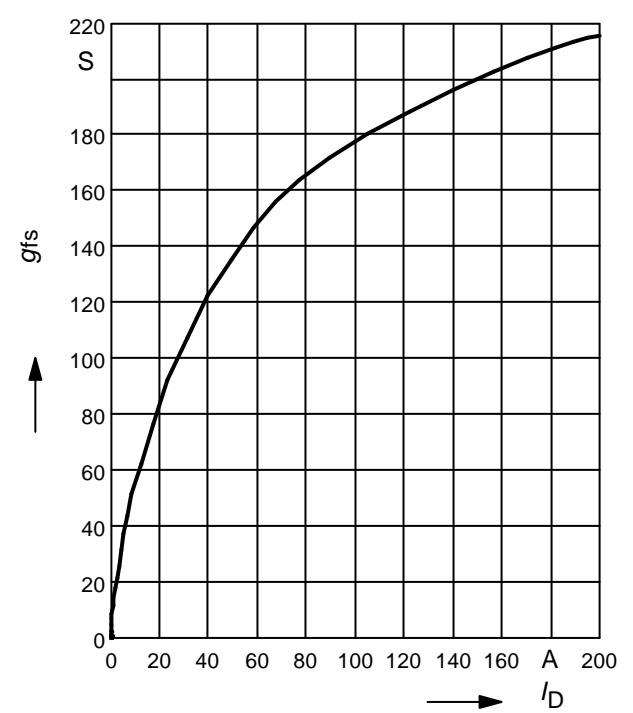
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$

parameter: g_{fs}



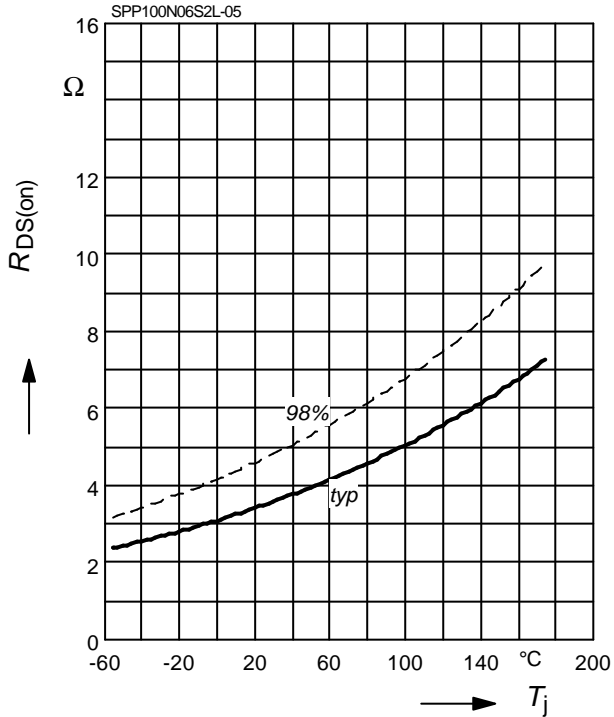


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9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

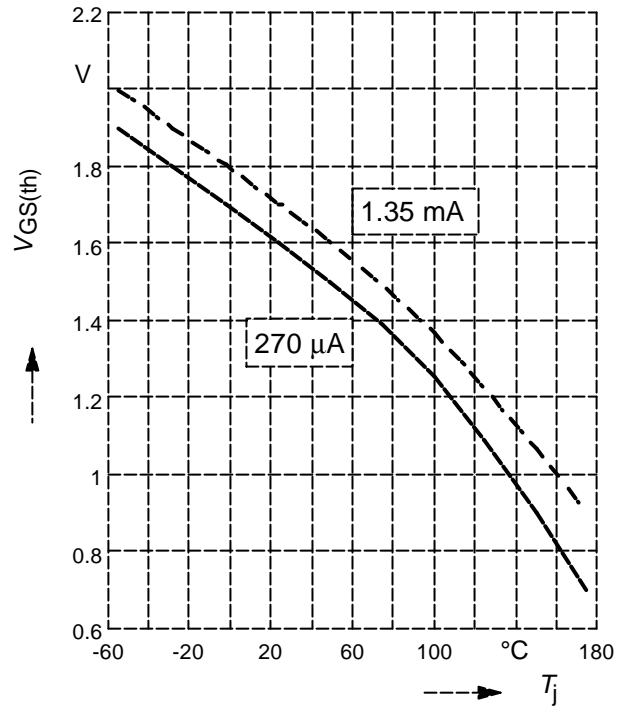
parameter: $I_D = 80\text{ A}$, $V_{GS} = 10\text{ V}$



10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$

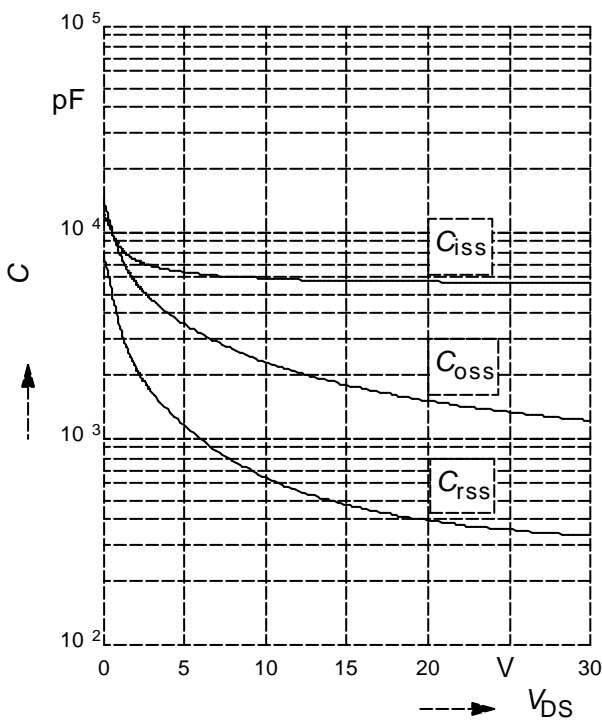
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$C = f(V_{DS})$

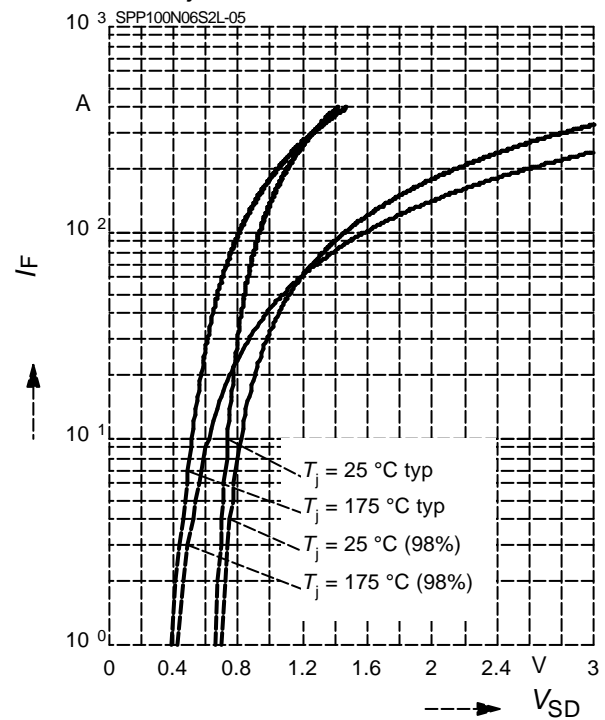
parameter: $V_{GS}=0\text{V}$, $f=1\text{ MHz}$



12 Forward character. of reverse diode

$I_F = f(V_{SD})$

parameter: T_j , $t_p = 80\text{ }\mu\text{s}$



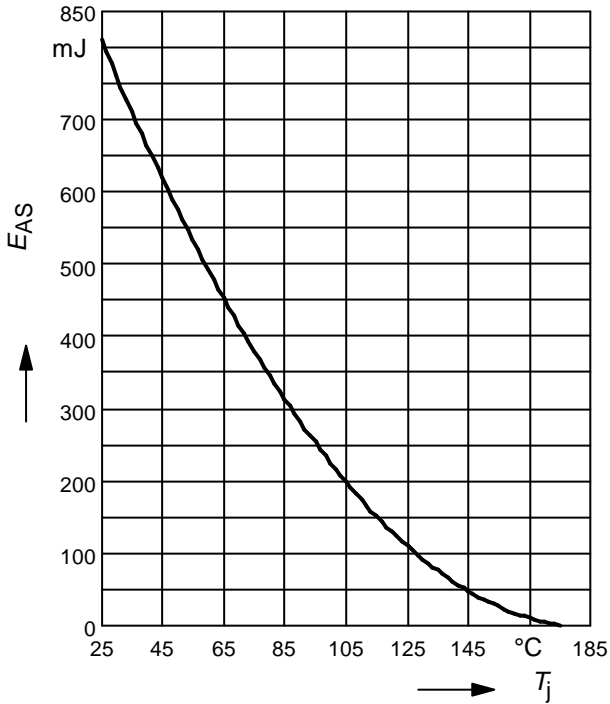


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13 Typ. avalanche energy

$E_{AS} = f(T_j)$

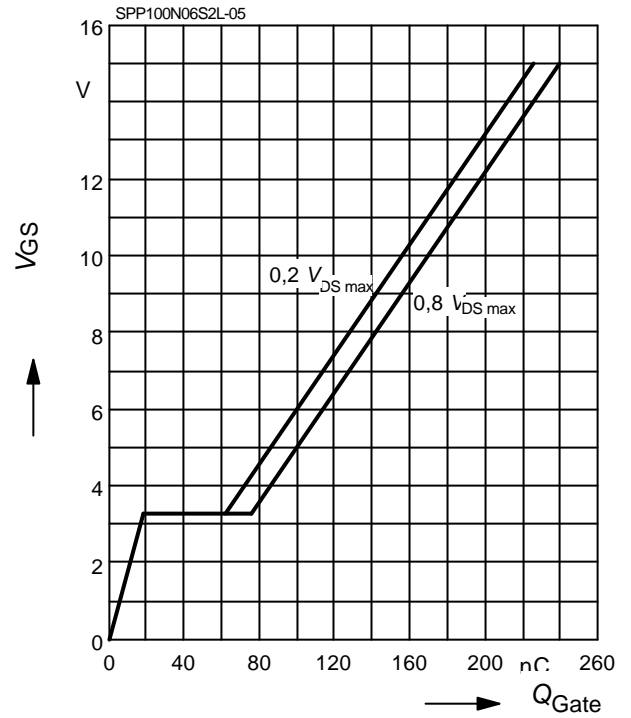
par.: $I_D = 80\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\ \Omega$



14 Typ. gate charge

$V_{GS} = f(Q_{Gate})$

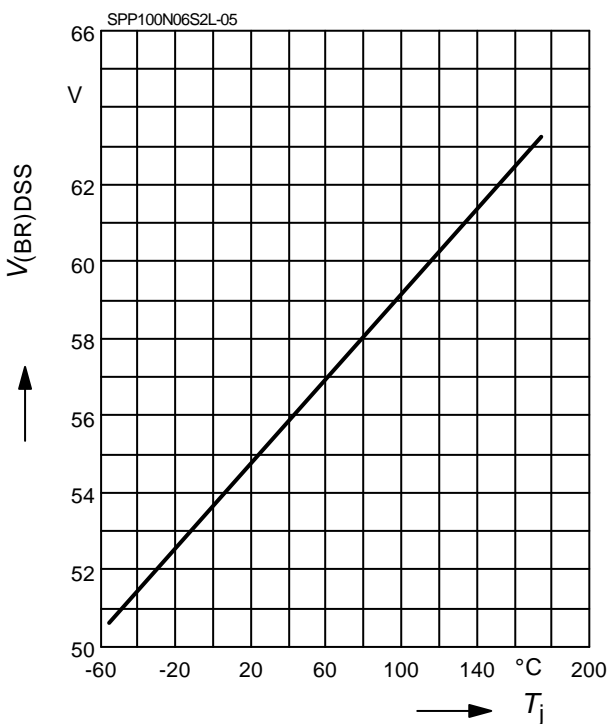
parameter: $I_D = 100\text{ A}$ pulsed



15 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$

parameter: $I_D = 10\text{ mA}$





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Further information

Please notice that the part number is **BSPP100N06S2L-05** and **BSPB100N06S2L-05**, for simplicity the device is referred to by the term **SPP100N06S2L-05** and **SPB100N06S2L-05** throughout this documentation.

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